

BUK7T1R4-100L

N-channel 100V, 1.35m Ω , Standard Level MOSFET in CCPAK1212i

26 August 2025

Product data sheet

1. General description

Automotive qualified N-channel MOSFET using the latest Trench 12 low ohmic split-gate technology, for ultra-low $R_{DS(on)}$ capability, housed in a CCPAK1212i (SOT8005A) package. This product has been fully designed and qualified to meet AEC-Q101 requirements delivering high performance and reliability.

2. Features and benefits

Fully automotive qualified to AEC-Q101:

175 °C rating suitable for thermally demanding automotive environments.

Trench 12 split-gate trench technology:

- Reduced cell pitch enables enhanced power density resulting in lower conduction losses.
- Fast and efficient switching with optimal damping for low spiking and improved switching efficiency.

CCPAK mounting base

 Large cross-sectional area of exposed drain tab for excellent thermal dissipation and low steady state thermal resistance.

CCPAK gull-wing leads:

- High Board Level Reliability (BLR), pins absorbing mechanical stress during thermal cycling.
- Visual (AOI) soldering inspection, no need for expensive x-ray equipment.

CCPAK copper clip technology:

- Low transient thermal resistance and package inductance.
- High maximum current capability and improved current spreading on silicon die.

3. Applications

- Light-electric / Electric vehicle applications
- 48V to 12V DC-DC Converters
- Synchronous rectifier for On-Board Charging (OBC) systems
- 48V Traction Inverters
- 48V Belt Starter Generator (BSG)
- Battery Management Systems

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	100	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	-	-	355	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	-	935	W
Tj	junction temperature		-55	-	175	°C



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 9</u>	-	1.07	1.35	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 10	-	2.4	3.1	mΩ
Dynamic cl	haracteristics			'	'	'
Q_{GD}	gate-drain charge	I _D = 25 A; V _{DS} = 50 V; V _{GS} = 10 V; T _j = 25 °C; <u>Fig. 11</u> ; <u>Fig. 12</u>	14	46	106	nC
Q _{G(tot)}	total gate charge	$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 ^{\circ}\text{C}$	-	228	-	nC

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source		
3	S	source	12 11 10 9 8 7	
4	S	source		
5	S	source		
6	G	gate] U	D
7	D	drain		
8	D	drain		G T T T
9	D	drain		mbb076 S
10	D	drain	1 2 3 4 5 6	
11	D	drain	sot8005a_sv	
12	D	drain	CCPAK1212i (SOT8005A)	
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BUK7T1R4-100L		Plastic, surface mounted copper clip package (CCPAK1212i); 12 terminals; 2.0 mm pitch, 12 mm × 12 mm × 2.5 mm body	SOT8005A			

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7T1R4-100L	X7T1R410L

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Tj = 25 °C unless otherwise stated.

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	100	V
V_{DGR}	drain-gate voltage	25 °C ≤ T _j ≤ 175 °C; R _{GS} = 20 kΩ		-	100	V
V_{GS}	gate-source voltage			-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	935	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	355	Α
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	355	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; Fig. 3		-	2195	А
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-drain o	diode			·		
I _S	source current	T _{mb} = 25 °C		-	355	А
I _{SM}	peak source current	pulsed; t _p ≤ 10 µs; T _{mb} = 25 °C		-	2195	Α
Avalanche rug	gedness			'	•	
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 99 A; $V_{sup} \le 100$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; t_p = 175 μs; Fig. 4	[1]	-	1130	mJ
I _{AS}	non-repetitive avalanche current	$V_{sup} = 100 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ $R_{GS} = 50 \Omega; Fig. 4$	[1]	-	99	A

[1] Protected by 100% test

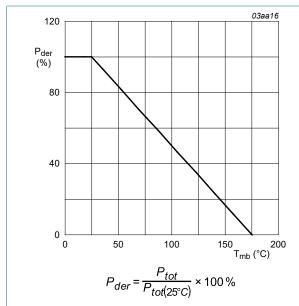
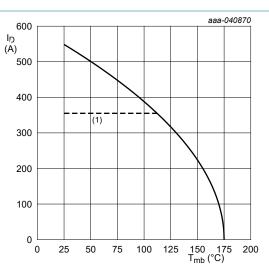
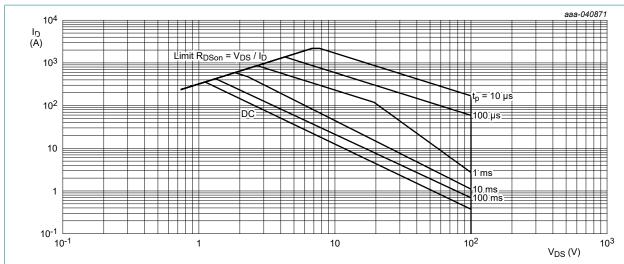


Fig. 1. Normalized total power dissipation as a function of mounting base temperature



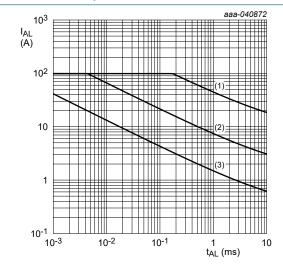
 $V_{GS} \ge 10 \text{ V}$ (1) 355 A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

Fig. 2. Continuous drain current as a function of mounting base temperature



T_{mb} = 25 °C; I_{DM} is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



(1) $T_{j \text{ (init)}} = 25 \text{ °C}$; (2) $T_{j \text{ (init)}} = 150 \text{ °C}$; (3) Repetitive Avalanche

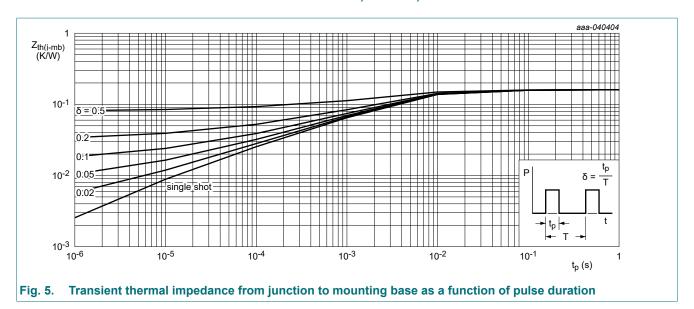
Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>		-	0.123	0.16	K/W
R _{th(j-a)}	thermal resistance from		[1]	-	30	-	K/W
	junction to ambient	With exposed pad contacting a fixed temperature heatsink. Thermal interface material is 50 µm thick and has 0.5W/ mK thermal conductivity.	[1]	-	1.2	-	K/W

^[1] Device on 4 layer PCB. Refer to TN00008 for further information.



10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static charac	teristics					
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _i = 25 °C	100	-	-	V
(511)500	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _i = -55 °C	90	-	-	V
V _{GS(th)}	gate-source threshold	I _D = 1 mA; V _{DS} =V _{GS} ; T _i = 25 °C	2	3.1	4	V
- 00(11)	voltage	I _D = 1 mA; V _{DS} =V _{GS} ; T _i = 175 °C	-	1.61	-	V
		$I_D = 1 \text{ mA; } V_{DS} = V_{GS;} T_i = -55 \text{ °C}$	_	3.7	_	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold	$25 \text{ °C} \leq T_i \leq 150 \text{ °C}$	_	-9.4	_	mV/K
_	voltage variation with temperature			0.1		
I _{DSS}	drain leakage current	V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C	-	0.05	1.6	μA
-033		V _{DS} = 100 V; V _{GS} = 0 V; T _i = 125 °C	-	35	160	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _i = 25 °C	-	2	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _i = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 9</u>	-	1.07	1.35	mΩ
	resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 100 °C; Fig. 10	-	1.7	2.2	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; Fig. 10	-	2.4	3.1	mΩ
		$V_{GS} = 7 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 9$	-	1.36	2.04	mΩ
R _G	gate resistance	f = 1 MHz; T _j = 25 °C	0.51	1.02	2.05	Ω
Dynamic cha	racteristics		•			
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 50 V; V _{GS} = 10 V; T _j = 25 °C; <u>Fig. 11</u> ; <u>Fig. 12</u>	128	255	383	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}$	-	228	-	nC
Q _{GS}	gate-source charge	I _D = 25 A; V _{DS} = 50 V; V _{GS} = 10 V;	46	76.5	107	nC
Q _{GS(th)}	pre-threshold gate- source charge	T _j = 25 °C; <u>Fig. 11; Fig. 12</u>	-	51	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge		-	25.4	-	nC
Q _{GD}	gate-drain charge		14	46	106	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 25 A; V _{DS} = 50 V; T _j = 25 °C; Fig. 11; Fig. 12	-	4.4	-	V
C _{iss}	input capacitance	V _{DS} = 50 V; V _{GS} = 0 V; f = 1 MHz;	10901	18168	25436	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 13</u>	2494	4157	6652	pF
C _{rss}	reverse transfer capacitance		9	92	239	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 2 \Omega; V_{GS} = 10 \text{ V};$	-	67	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C$	-	63	-	ns
$t_{d(off)}$	turn-off delay time	1	-	157	-	ns
t _f	fall time	1	-	84	-	ns
Source-drain	diode			1	1	1
V _{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _i = 25 °C; <u>Fig. 14</u>	-	0.76	1	V

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{rr}		$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	62	-	ns
Q _r	recovered charge	V _{DS} = 50 V; T _j = 25 °C; <u>Fig. 15</u>	-	74	-	nC

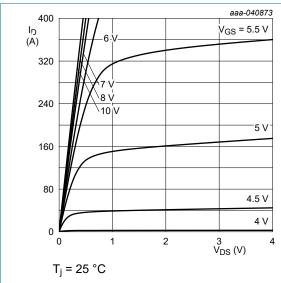


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

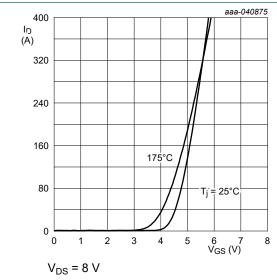


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

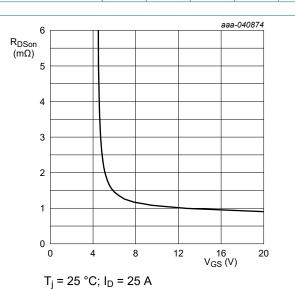


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

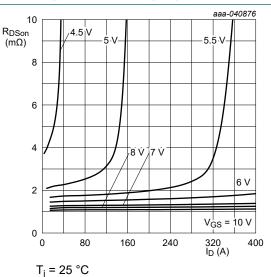


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

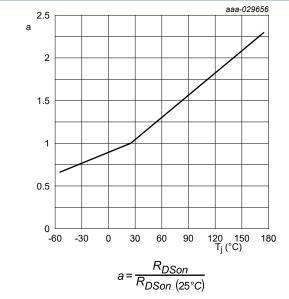


Fig. 10. Normalized drain-source on-state resistance factor as a function of junction temperature

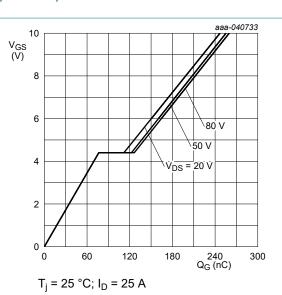


Fig. 11. Gate-source voltage as a function of gate charge; typical values

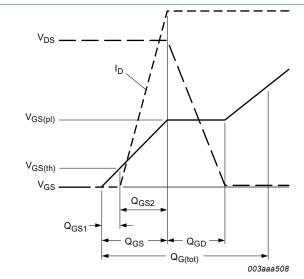
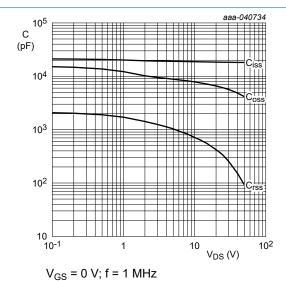


Fig. 12. Gate charge waveform definitions



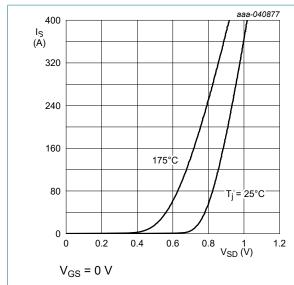


Fig. 14. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

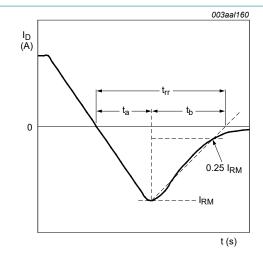
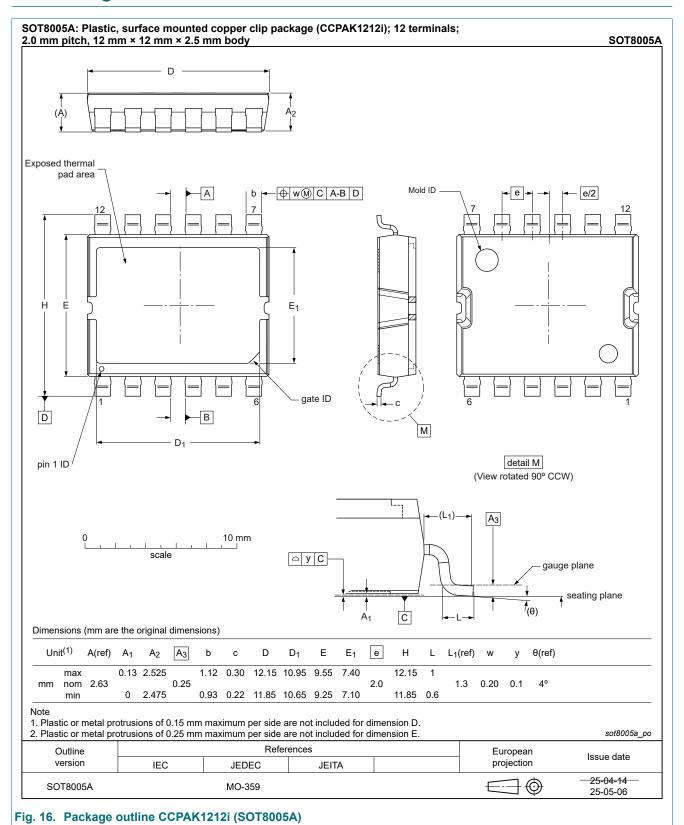
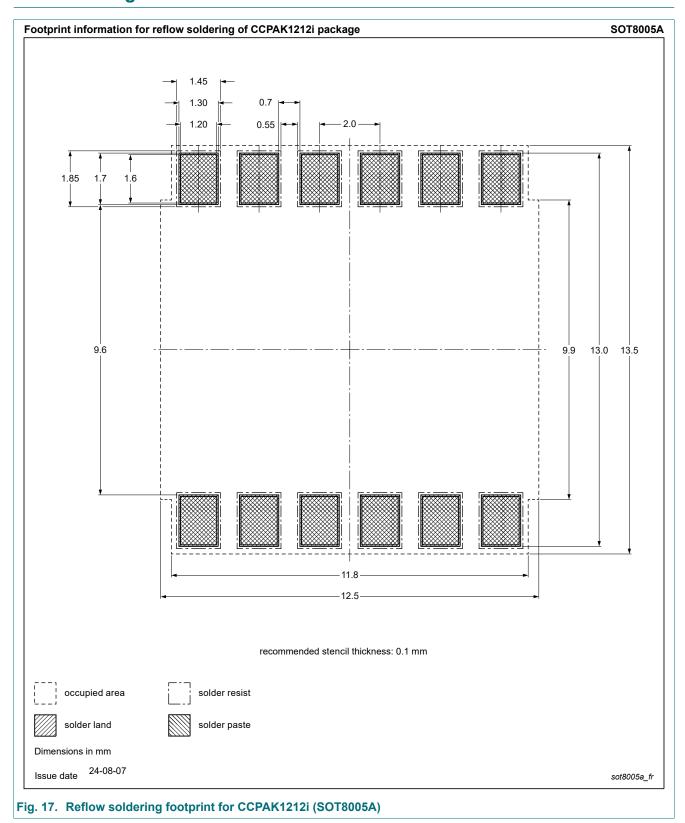


Fig. 15. Reverse recovery timing definition

11. Package outline



12. Soldering



13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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